## NSN 5962-01-279-0149

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Body Length:
Between 0.442 inches and 0.458 inches
Body Width:
Between 0.442 inches and 0.458 inches
Body Height:
Between 0.064 inches and 0.100 inches
Maximum Power Dissipation Rating:
1.2 watts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
Features Provided:
Programmable and monolithic and bipolar
Inclosure Material:
Ceramic
Inclosure Configuration:
Leadless flat pack
Output Logic Form:
Transistor-transistor logic
Input Circuit Pattern:
20 input
Case Outline Source And Designator:
C-4 mil-m-38510
Current Rating Per Characteristic:
100.00 milliamperes forward current, nonrepetitive, peak total value
Terminal Surface Treatment:
Solder
Product Name:
20-input 8-output and-or invert gate array
Voltage Rating And Type Per Characteristic:
12.0 volts power source
Time Rating Per Chacteristic:
50.00 nanoseconds propagation delay time, low to high level output and 50.00 nanoseconds propagation delay time, high to low level
output
Memory Device Type:
Pal
Test Data Document:

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

28 leadless

**Terminal Type And Quantity:** 

Shelf Life:

N/a

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Demilitarization:

No

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